
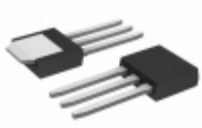



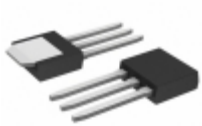
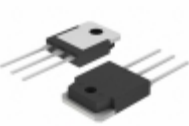

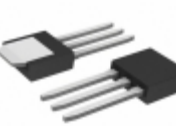
	<h2 style="color: #E67E22;">GP2M008A060FGH</h2>	
	Hersteller-Teilenummer:	GP2M008A060FGH
	Hersteller / Marke:	Global Power Technologies Group
	Teil der Beschreibung:	MOSFET N-CH 600V 7.5A TO220F
Datenblätter:	 GP2M008A060FGH.pdf	
RoHs Status:	Bleifrei / RoHS-konform	
Lagerzustand:	New original, 1894 pcs Stock Available.	
Liefern von:	Hong Kong	
Versandweg:	DHL/Fedex/TNT/UPS/EMS	
<p>Image may be representation. See specs for product details.</p>		

Spezifikationen

Teilenummer	GP2M008A060FGH
Hersteller	Global Power Technologies Group
Beschreibung	MOSFET N-CH 600V 7.5A TO220F
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	1894 pcs Stock
Serie	-
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Through Hole
Verpackung / Gehäuse	TO-220-3 Full Pack
Supplier Device-Gehäuse	TO-220F
Verlustleistung (max)	39W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	600V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	7.5A (Tc)
Rds On (Max) @ Id, Vgs	1.2 Ohm @ 3.75A, 10V
VGS (th) (Max) @ Id	5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	23nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	1063pF @ 25V
Verpackung	Tube

GP2M008A060FGH ist neu im Original, Suche GP2M008A060FGH Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie GP2M008A060FGH Global Power Technologies Group mit Garantie und Vertrauen. Anfrage GP2M008A060FGH: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>GP2M005A060PGH Global Power Technologies Group MOSFET N-CH 600V 4.2A IPAK</p>	 <p>GP2M008A060FG Global Power Technologies Group MOSFET N-CH 600V 7.5A TO220F</p>	 <p>GP2M007A080F Global Power Technologies Group MOSFET N-CH 800V 7A TO220F</p>	 <p>GP2M009A090FG Global Power Technologies Group MOSFET N-CH 900V 9A TO220F</p>
 <p>GP2M008A060PG Global Power Technologies Group MOSFET N-CH 600V 7.5A IPAK</p>	 <p>GP2M009A090NG Global Power Technologies Group MOSFET N-CH 900V 9A TO3PN</p>	 <p>GP2M007A065HG Global Power Technologies Group MOSFET N-CH 650V 6.5A TO220</p>	 <p>GP2M008A060PGH Global Power Technologies Group MOSFET N-CH 600V 7.5A IPAK</p>

heiße Teile

Mehr

⚙ GP200EMTR-G1	↔ GP200MTR-G1	⇒ GP2A231LRSA	D GP2A25J0000F	↔ GP2A25J0000F
⊣ GP2A25NJ	⚙ GP2A28A1J00F	D GP2A28N1J00F	⇒ GP2AP002A00F	↔ GP2AP002S00F
⚙ GP2AP003A10F	⊣ GP2AP007A00F	⚙ GP2AP008T00F	↔ GP2AP030A00F	↔ GP2AP052A00F
D GP2AP052A00F	⚙ GP2L26K2	⊣ GP2M002A060FG	⚙ GP2M004A060PG	↔ GP2M004A065FG
⇒ GP2M004A065PG	↔ GP2M005A050PG	⚙ GP2M005A060CG	⊣ GP2M005A060FG	↔ GP2M005A060PGH
↔ GP2M010A060F	⇒ GP2M010A065F	D GP2M011A090NG	⚙ GP2M012A080NG	⊣ GP2M020A050H
⚙ GP2M020A060N	D GP2S24J0000F	⇒ GP2S27T3	↔ GP2S27T3J00F	↔ GP2S27V6
⊣ GP2S29SVJ00F	⚙ GP2S40JJ000F	↔ GP2S700HCP	⇒ GP2S700HCP	↔ GP2W0004YP
⚙ GP2W0110YPS	⊣ GP2W0112YPOF	⚙ GP2W0118YPS	D GP2W0150YP0F	↔ GP2W3104XP0F
↔ GP2W3104YP0F	⚙ GP2W3106YP0F	⊣ GP2W3152YP0F	⚙ GP2W3172XP0F	↔ GP2W3270XP0F

Contact us: Info@Y-IC.com

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